

勝特力材料 886-3-5753170
 勝特力电子(上海) 86-21-34970699
 勝特力电子(深圳) 86-755-83298787
 Http://www.100y.com.tw



CHENMKO ENTERPRISE CO.,LTD

SURFACE MOUNT

P-Channel Enhancement Mode Field Effect Transistor

VOLTAGE 30 Volts CURRENT 1.9 Ampere

CHT2303PT

APPLICATION

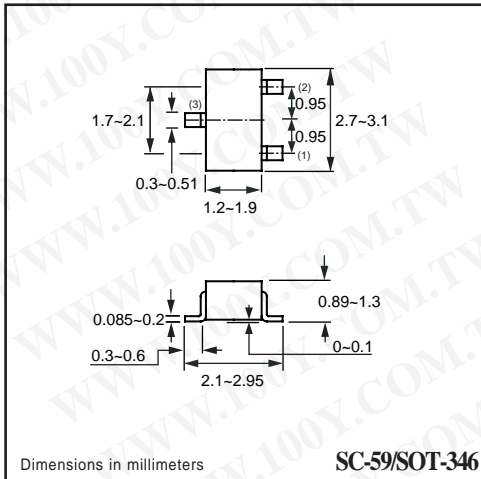
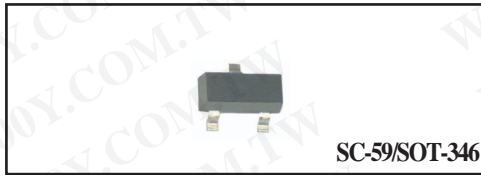
- * Servo motor control.
- * Power MOSFET gate drivers.
- * Other switching applications.

FEATURE

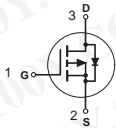
- * Small flat package. (SC-59)
- * High density cell design for extremely low R_{DS(ON)}.
- * Rugged and reliable.
- * High saturation current capability.

CONSTRUCTION

- * P-Channel Enhancement



CIRCUIT



Absolute Maximum Ratings

T_A = 25°C unless otherwise noted

Symbol	Parameter	CHT2303PT	Units
V _{DSS}	Drain-Source Voltage	-30	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Maximum Drain Current - Continuous	-1.9	A
	- Pulsed (Note 3)	10	
P _D	Maximum Power Dissipation	1250	mW
T _J	Operating Temperature Range	-55 to 150	°C
T _{STG}	Storage Temperature Range	-55 to 150	°C

Note : 1. Surface Mounted on FR4 Board , t <= 10sec
 2. Pulse Test , Pulse width <= 300us , Duty Cycle <= 2%
 3. Repetitive Rating , Pulse width limited by maximum junction temperature
 4. Guaranteed by design , not subject to production trsting

Thermal characteristics

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RATING CHARACTERISTIC CURVES (CHT2303PT)

Electrical Characteristics $T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Units
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OFF CHARACTERISTICS

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -30\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
I_{GSSF}	Gate-Body Leakage	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			+100	nA
I_{GSSR}	Gate-Body Leakage	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

ON CHARACTERISTICS (Note 2)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-1		-3	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS} = -10\text{ V}, I_D = -1.7\text{ A}$		150	200	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -1.3\text{ A}$		230	320	
g_{FS}	Forward Transconductance	$V_{DS} = -10\text{ V}, I_D = -1.7\text{ A}$		2.4		S

SWITCHING CHARACTERISTICS (Note 4)

Q_g	Total Gate Charge	$V_{DS} = -15\text{ V}, I_D = -1.7\text{ A}$		6.0	10	nC	
Q_{gs}	Gate-Source Charge		$V_{GS} = -10\text{ V}$		0.8		
Q_{gd}	Gate-Drain Charge				1.5		
t_{on}	Turn-On Time	$V_{DD} = -15\text{ V}$ $I_D = -1.0\text{ A}, V_{GS} = -10\text{ V}$ $R_{GEN} = 6\ \Omega$		10	20	nS	
t_r	Rise Time			10	20		
t_{off}	Turn-Off Time			20	35		
t_f	Fall Time			6	20		

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS

I_S	Drain-Source Diode Forward Current (Note 1)				-1.25	A
V_{SD}	Drain-Source Diode Forward Voltage	$I_S = -1.25\text{ A}, V_{GS} = 0\text{ V}$ (Note 2)			-1.2	V

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RATING CHARACTERISTIC CURVES (CHT2303PT)

Typical Electrical Characteristics

Figure 1. Output Characteristics

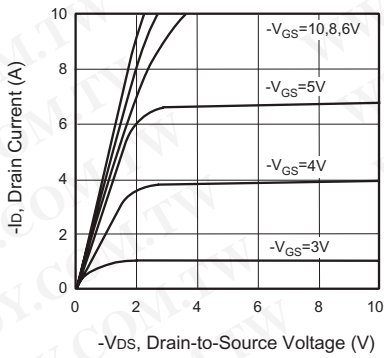


Figure 2. Transfer Characteristics

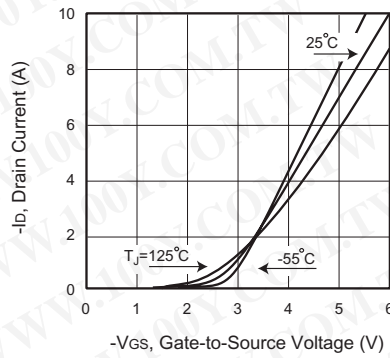


Figure 3. Capacitance

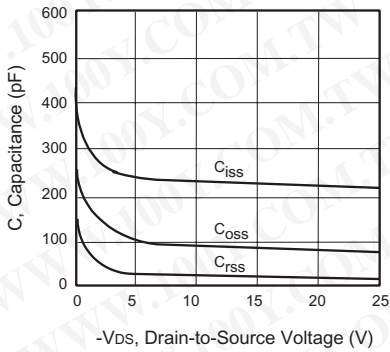


Figure 4. On-Resistance Variation with Temperature

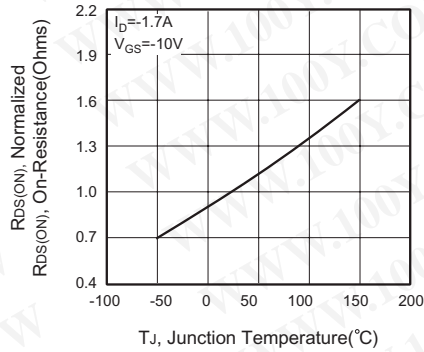


Figure 5. Gate Threshold Variation with Temperature

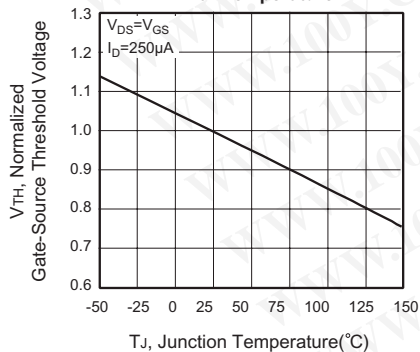


Figure 6. Body Diode Forward Voltage Variation with Source Current

